

ABSTRACT OF THE DISCLOSURE

A high power semiconductor device in which there are a plurality of gate electrodes includes: an active region of an approximately rectangular shape which is formed on a semiconductor substrate; a drain electrode which is formed on the active region; and a first and a second source electrodes which are disposed on the both sides to the drain electrode in such a manner that the first and the second source electrodes face each other across the gate electrodes. The directions of currents carried by the first and the second source electrodes are opposite to each other.